HALOGEN

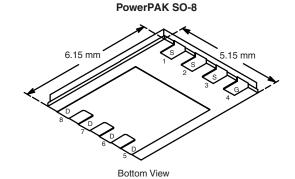
FREE





# P-Channel 150 V (D-S) MOSFET

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	$R_{DS(on)}\left(\Omega\right)$	I <sub>D</sub> (A)			
- 150	$0.090 \text{ at V}_{GS} = -10 \text{ V}$	- 5.2			
	0.095 at V <sub>GS</sub> = - 6 V	- 5.0			



Ordering Information: Si7439DP-T1-E3 (Lead (Pb)-free)

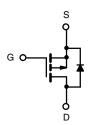
Si7439DP-T1-GE3 (Lead (Pb)-free and Halogen-free)

#### **FEATURES**

- Halogen-free According to IEC 61249-2-21 **Definition**
- TrenchFET® Power MOSFETs
- Ultra-Low On-Resistance Critical for Application COMPLIANT
- Low Thermal Resistance PowerPAK®Package with Low 1.07 mm Profile
- 100 % Rg and Avalanche Tested
- Compliant to RoHS Directive 2002/95/EC

### **APPLICATIONS**

Active Clamp in Intermediate DC/DC Power Supplies



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	(T <sub>A</sub> = 25 °C, unle	ess otherwise	noted)		
Parameter	Symbol	10 s	Steady State	Unit	
Drain-Source Voltage		V <sub>DS</sub>	- 150		V
Gate-Source Voltage	V <sub>GS</sub>	± 20		V	
Continuous Drain Current /T 150 °C\a	T <sub>A</sub> = 25 °C	- I <sub>D</sub>	- 5.2	- 3.0	
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> = 70 °C		- 4.1	- 2.4	
Pulsed Drain Current		I <sub>DM</sub>	- 50		Α
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	- 4.2	- 1.6	
Single Pulse Avalanche Current		I <sub>AS</sub>	- 40		
Single Pulse Avalanche Energy  L = 0.1 mH		E <sub>AS</sub>	80		mJ
Mariana Parana Disabational	T <sub>A</sub> = 25 °C	- P <sub>D</sub>	5.4	1.9	W
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 70 °C		3.4	1.2	VV
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150		°C
Soldering Recommendations (Peak Temperature		260		· ()	

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Marrian and Lunckian to Ambients	t ≤ 10 s	R <sub>thJA</sub>	18	23		
Maximum Junction-to-Ambient <sup>a</sup>	Steady State	' 'thJA	50	65	°C/W	
Maximum Junction-to-Case (Drain)	Steady State	R <sub>thJC</sub>	1.0	1.5		

#### Notes:

- a. Surface mounted on 1" x 1" FR4 board.
- b. See solder profile (www.vishay.com/ppg?73257). The PowerPAK SO-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- c. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

# Vishay Siliconix



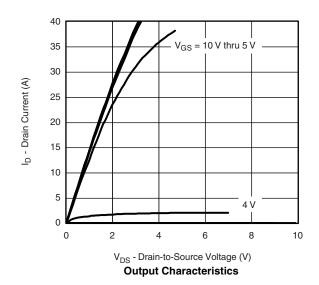
<b>SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C, unless otherwise noted)							
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 2.0		- 4.0	V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zava Cata Valtaga Dvain Current	1	V <sub>DS</sub> = - 150 V, V <sub>GS</sub> = 0 V			- 1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = - 150 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 70 °C		- 10	μΑ		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = - 10 V, V <sub>GS</sub> = - 10 V	- 30			Α	
D : 0	В	V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 5.2 A		0.073 0.090		0	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 6 V, I <sub>D</sub> = - 5.0 A		0.077	0.095	Ω	
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 5.2 A		19		S	
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	I <sub>S</sub> = - 4.2 A, V <sub>GS</sub> = 0 V		- 0.78	- 1.2	V	
Dynamic <sup>b</sup>							
Total Gate Charge	Qg			88	135		
Gate-Source Charge	$Q_{gs}$	$V_{DS} = -75 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -5.2 \text{ A}$		17.5		nC	
Gate-Drain Charge	$Q_{gd}$			26.5			
Gate Resistance	$R_g$		1.5	3	4.5	Ω	
Turn-On Delay Time	t <sub>d(on)</sub>			25	40		
Rise Time	t <sub>r</sub>	$V_{DD}$ = - 75 V, $R_L$ = 15.5 $\Omega$		46	70		
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D\cong$ - 4.8 A, $V_{GEN}$ = - 10 V, $R_G$ = 6 $\Omega$		115	180	ns	
Fall Time	t <sub>f</sub>			64	100		
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = - 2.9 A, dI/dt = 100 A/μs		100	150		

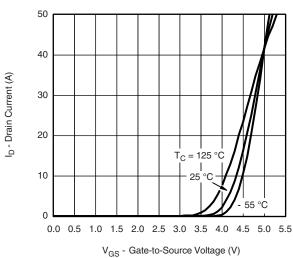
#### Notes:

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



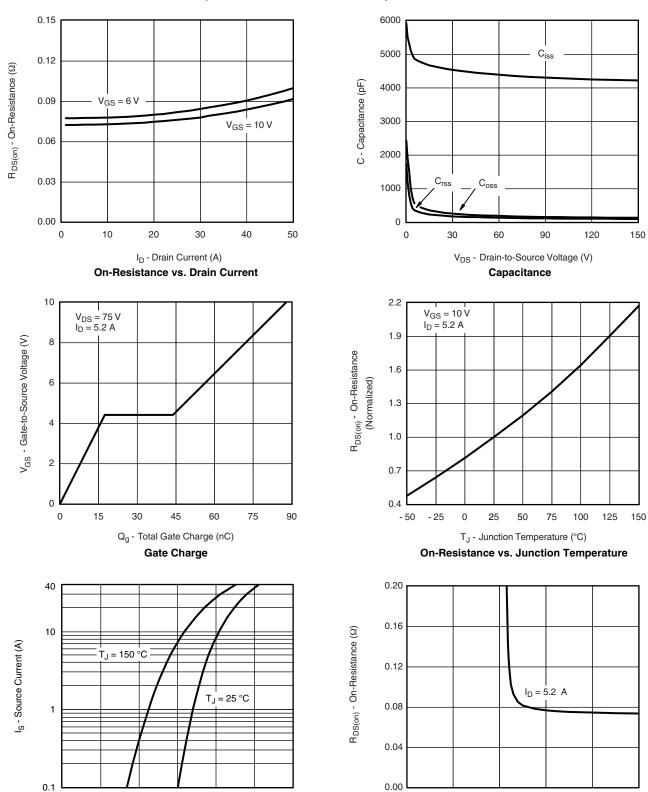


**Transfer Characteristics** 





### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



On-Resistance vs. Gate-to-Source Voltage

 $V_{\text{GS}}$  - Gate-to-Source Voltage (V)

0

0.2

0.4

0.6

 $V_{SD}$  - Source-to-Drain Voltage (V)

Source-Drain Diode Forward Voltage

0.8

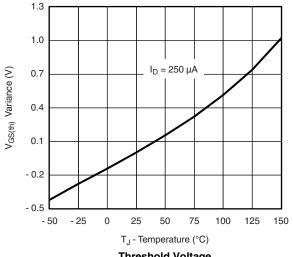
1.0

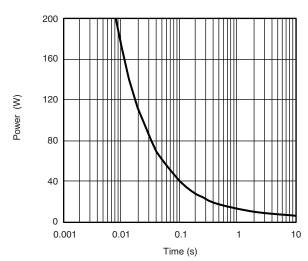
1.2

10

# Vishay Siliconix

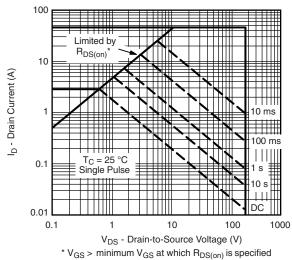
## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



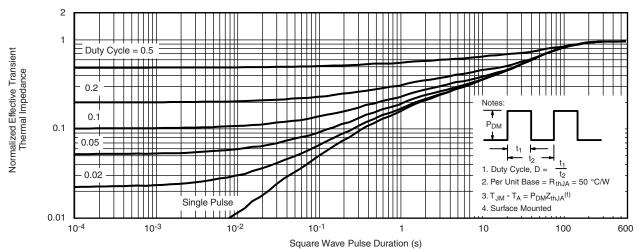


**Threshold Voltage** 

Single Pulse Power



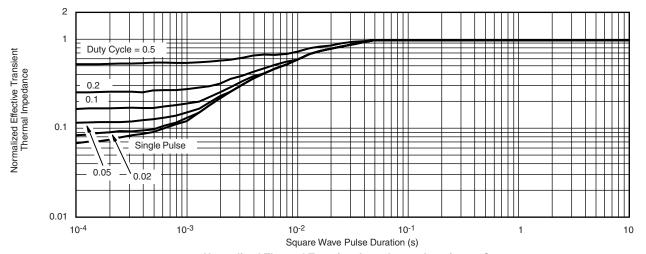




Normalized Thermal Transient Impedance, Junction-to-Ambient



### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



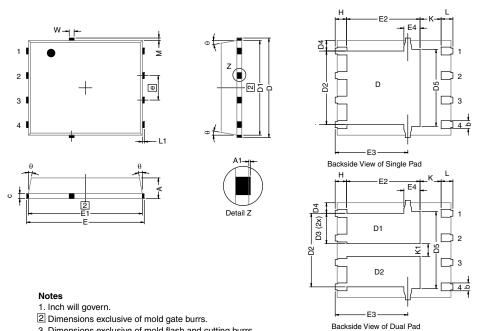
Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg?73106">www.vishay.com/ppg?73106</a>.



DWG: 5881

# PowerPAK® SO-8, (Single/Dual)



	3. Dimensions exclusive of moid flash and cutting burrs.							
DIM.		MILLIMETERS		INCHES				
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.		
A	0.97	1.04	1.12	0.038	0.041	0.044		
A1		-	0.05	0	-	0.002		
b	0.33	0.41	0.51	0.013	0.016	0.020		
С	0.23	0.28	0.33	0.009	0.011	0.013		
D	5.05	5.15	5.26	0.199	0.203	0.207		
	4.00	4.00	F 00	0.400	0.400	0.407		

Α	0.97	1.04	1.12	0.038	0.041	0.044	
A1		-	0.05	0	-	0.002	
b	0.33	0.41	0.51	0.013	0.016	0.020	
С	0.23	0.28	0.33	0.009	0.011	0.013	
D	5.05	5.15	5.26	0.199	0.203	0.207	
D1	4.80	4.90	5.00	0.189	0.193	0.197	
D2	3.56	3.76	3.91	0.140	0.148	0.154	
D3	1.32	1.50	1.68	0.052	0.059	0.066	
D4		0.57 typ.			0.0225 typ.		
D5		3.98 typ.			0.157 typ.		
E	6.05	6.15	6.25	0.238	0.242	0.246	
E1	5.79	5.89	5.99	0.228	0.232	0.236	
E2 (for AL product)	3.30	3.48	3.66	0.130	0.137	0.144	
E2 (for other product)	3.48	3.66	3.84	0.137	0.144	0.151	
E3	3.68	3.78	3.91	0.145	0.149	0.154	
E4 (for AL product)		0.58 typ.		0.023 typ.			
E4 (for other product)		0.75 typ.			0.030 typ.		
е		1.27 BSC			0.050 BSC		
K (for AL product)		1.45 typ.			0.057 typ.		
K (for other product)		1.27 typ.			0.050 typ.		
K1	0.56	-	=	0.022	-	=	
Н	0.51	0.61	0.71	0.020	0.024	0.028	
L	0.51	0.61	0.71	0.020	0.024	0.028	
L1	0.06	0.13	0.20	0.002	0.005	0.008	
θ	0°	-	12°	0°	-	12°	
W	0.15	0.25	0.36	0.006	0.010	0.014	
M	0.125 typ.			0.005 typ.			
ECN: C13-0702-Rev. K, 20	)-May-13			•			

Revison: 20-May-13 Document Number: 71655



## RECOMMENDED MINIMUM PADS FOR PowerPAK® SO-8 Single



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index

APPLICATION NOTE



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Vishay

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Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Vishay documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.

Revision: 02-Oct-12 Document Number: 91000